

Unravelling the complex optical properties of heterogeneous transparent and conducting vanadates thin films grown on a 2D nanosheet layer by the means of Spectroscopic Ellipsometry

A. Boileau¹, **Simon Hurand**², F. Baudouin³, U. Lüders¹, M. Dallochio¹, B. Bérini⁵, A. Cheikh¹, A. David¹, F. Paumier², T. Girardeau², P. Marie⁶, C. Labbé⁶, J. Cardin⁶, D. Aureau⁷, M. Frégnaux⁷, M. Guilloux-Viry³, W. Prellier¹, Y. Dumont⁵, V. Demange³, A. Fouchet¹

¹ Normandie Univ, ENSICAEN, UNICAEN, CNRS, CRISMAT, 14000 CAEN, France

² Institut Pprime, UPR 3346 CNRS-Université de Poitiers-ENSMA, SP2MI, 86962 Futuroscope-Chasseneuil Cedex, France

³ Univ Rennes, CNRS, ISCR – UMR 6226, ScanMAT – UMS 2001, F-35000 Rennes, France

⁴ Univ Rennes, CNRS, IPR – UMR 6251, F-35000 Rennes, France

⁵ GEMaC, Université Paris-Saclay, UMR 8635 CNRS- Université de Versailles Saint-Quentin en Yvelines, Versailles, France

⁶ CIMAP, ENSICAEN – UNICAEN – CNRS, Caen, France

⁷ ILV, CNRS UMR 8180, Université de Versailles Saint-Quentin-en-Yvelines – Université Paris-Saclay, Versailles 78035, France



I – Context

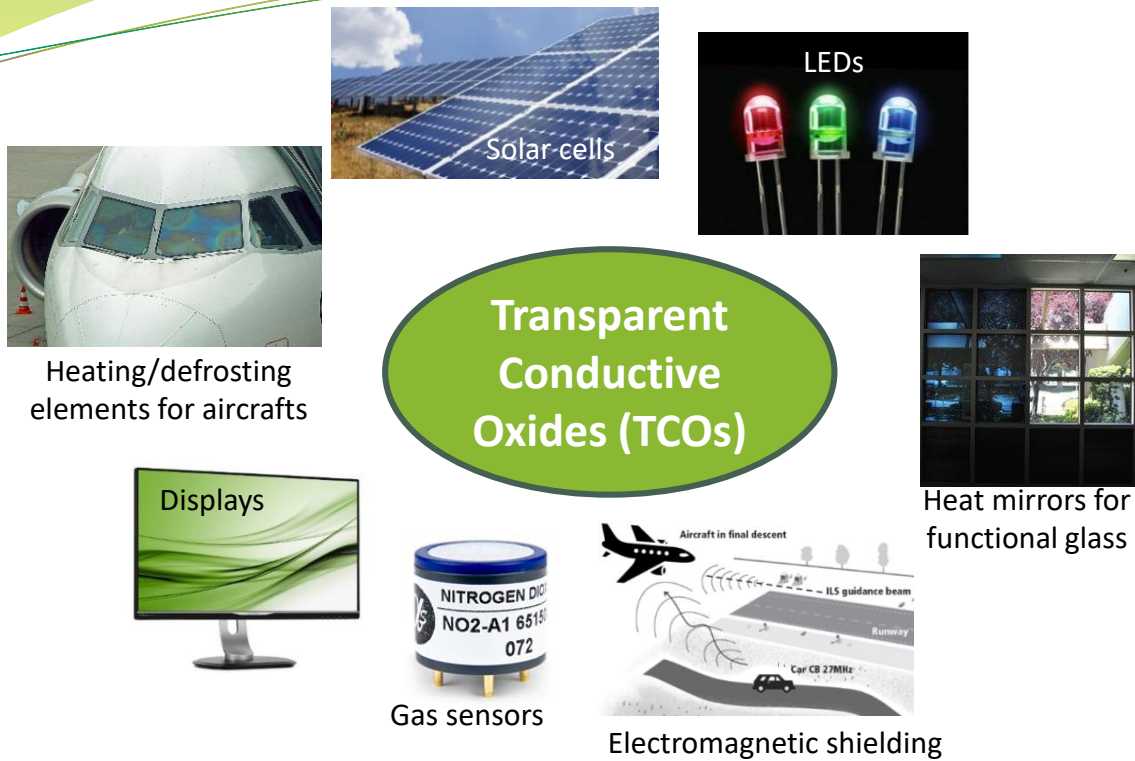
II – Structural properties

III – Optical properties through Effective Medium

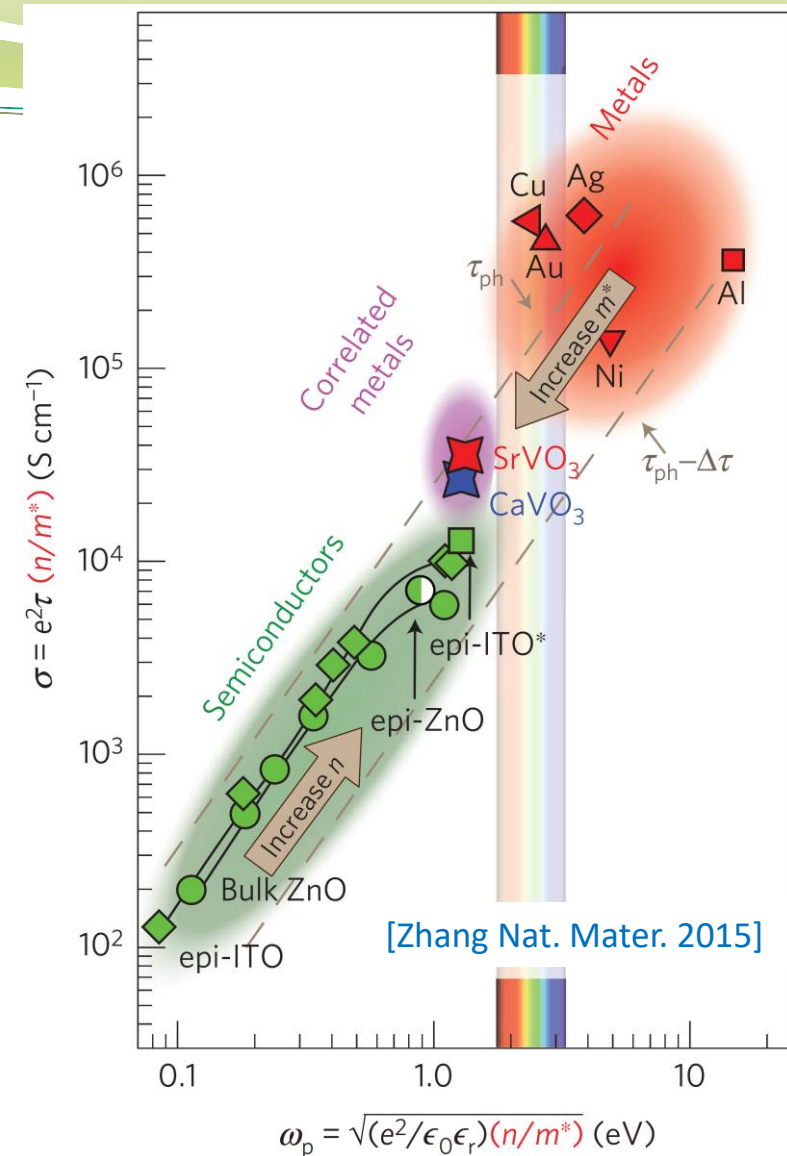
IV – Infrared properties

IV – Conclusions

Context



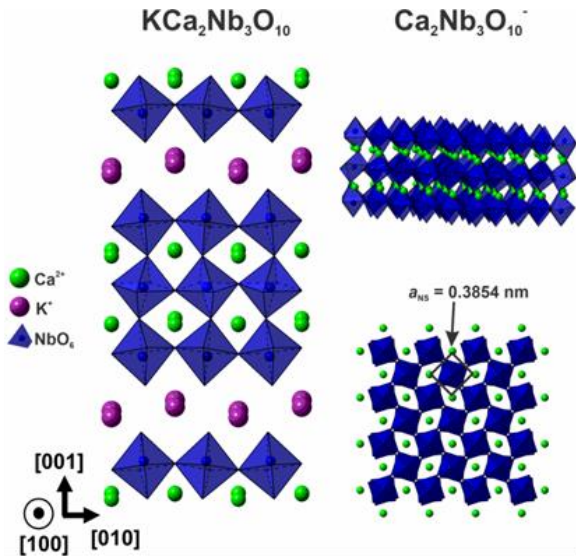
- Indium Tin Oxide (ITO) : best FOM and most used
Degenerated semiconductor, $N_e \sim 10^{20} e^- \cdot cm^{-3}$
- Indium scarcity → search for alternatives
- $CaVO_3$ and $SrVO_3$ Vanadates : as good as ITO
Metallic, $N_e \sim 10^{22} e^- \cdot cm^{-3}$
+ Strong correlation → plasma frequency in IR range



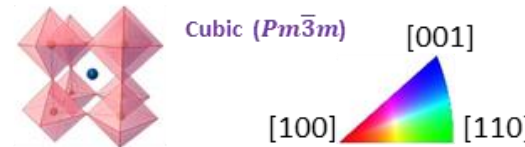
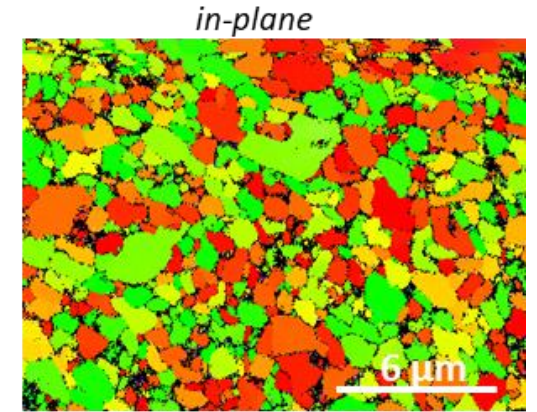
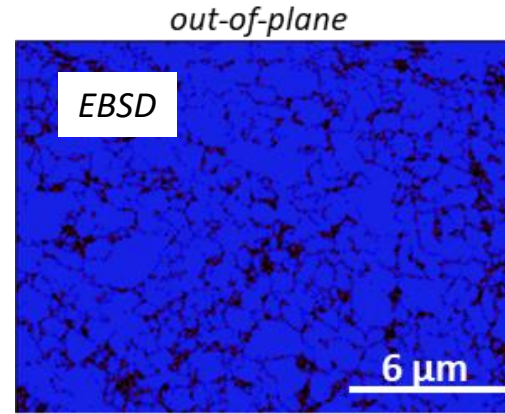
- Limitation : high-temperature epitaxial growth on specific textured substrate (STO, LSAT...)
→ How to transfer it on any substrate (e.g. glass) ??

Vanadates growth on Nanosheet template

- Nanosheet (NS) deposition by Langmuir-Blodgett :



- Pulsed Laser Deposition of CaVO_3 / SrVO_3 @ 400 to 700 °C



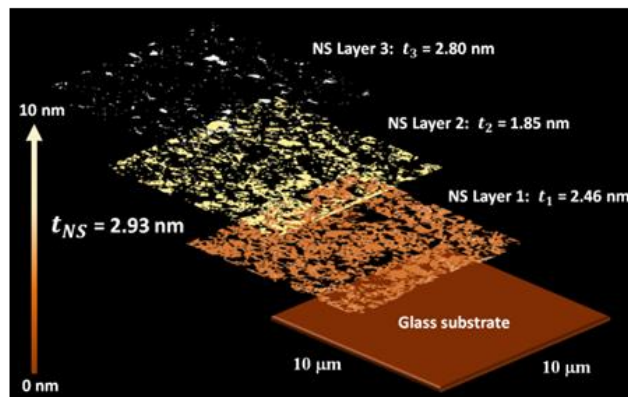
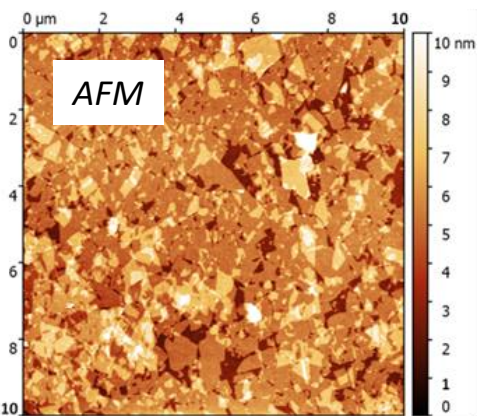
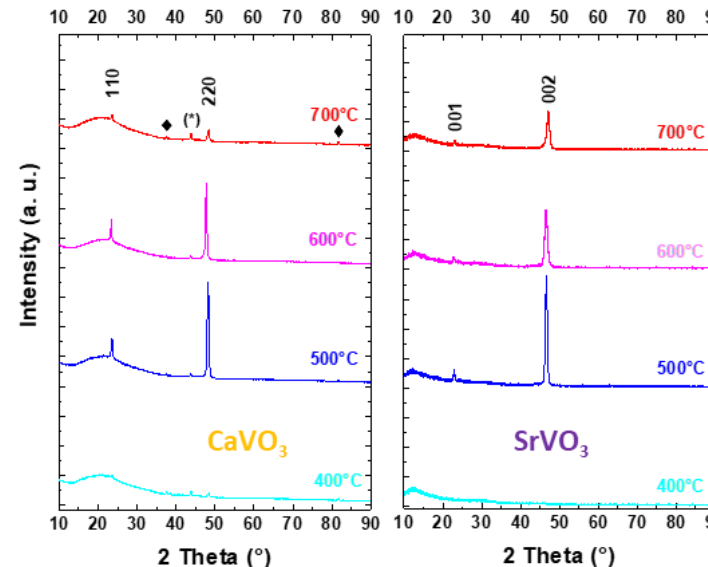
SrVO_3 500°C

Textured epitaxial growth

Crystalline coverage ~70 %
(30 % = amorphous vanadates)

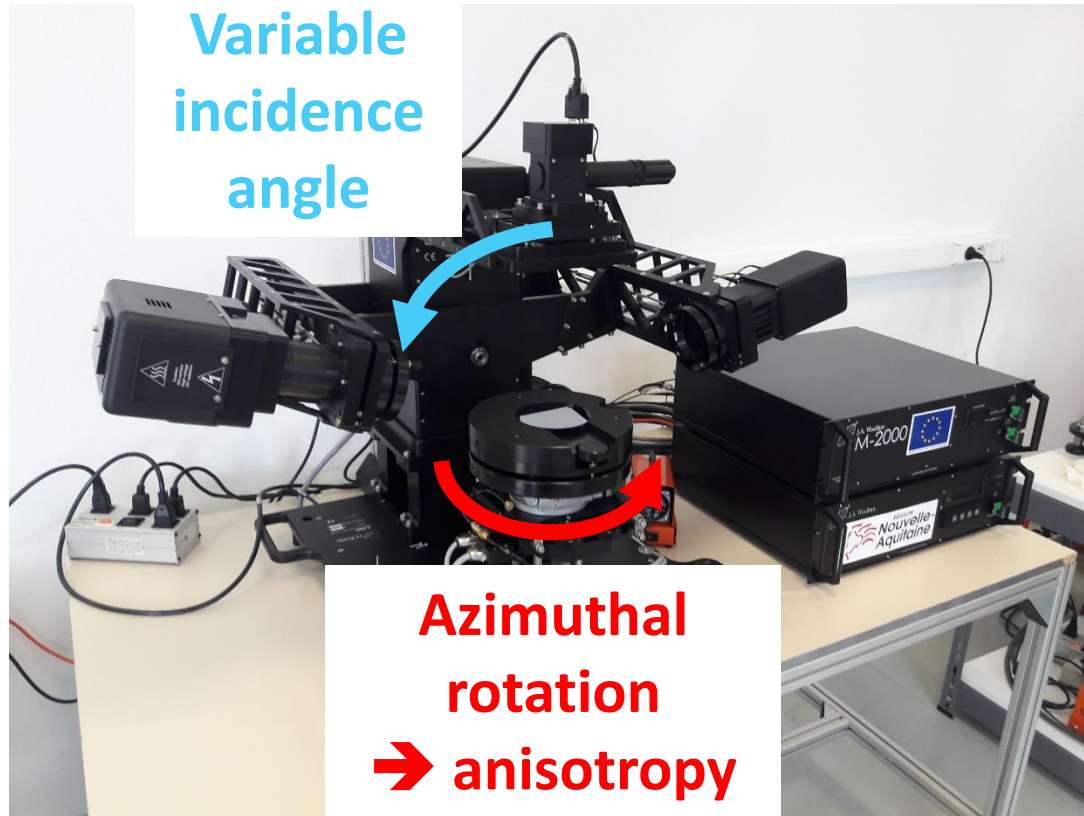
Growth temperature :

- 400 °C : amorphous
- 500-600 °C : nice cristallinity
- 700 °C : degraded



- NS coverage ~ 70 % (30 % = bare Glass substrate)
- ~ 3 NS layers

Optical Properties : Ellipsometry @ Institut Pprime, Poitiers



Woollam M2000XI

UV-visible-NIR : 211 nm – 1700 nm



Woollam Vase-IR Mark II

IR : 1.7 μm – 40 μm

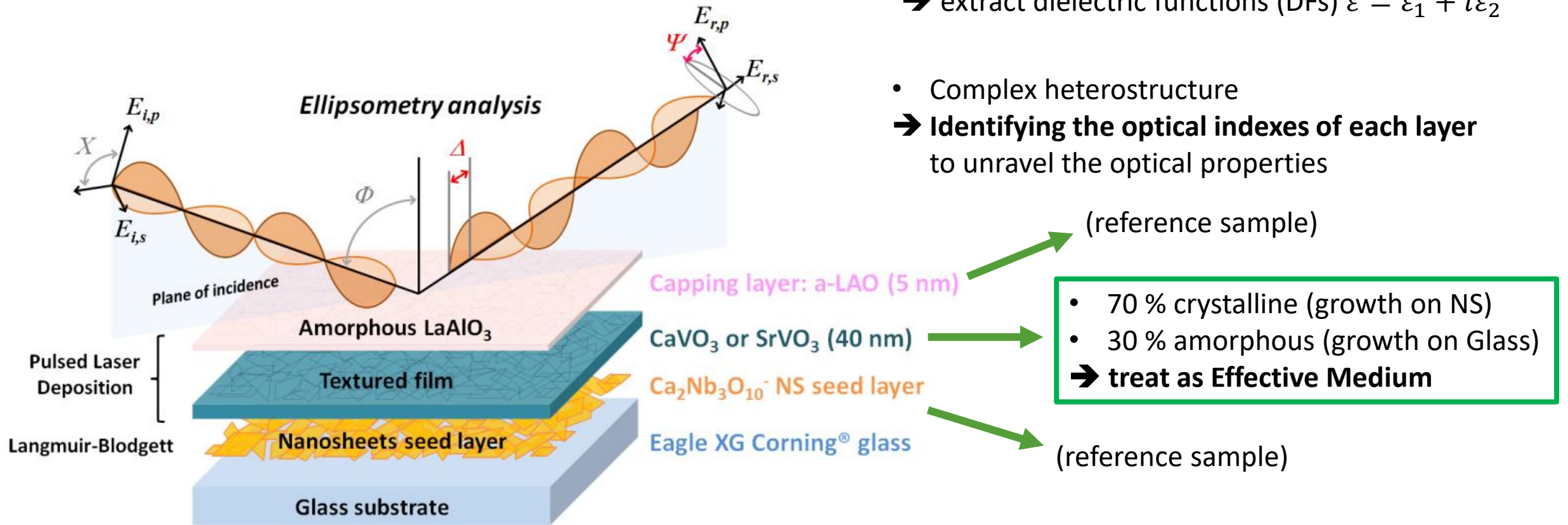
Cryostat 77 K - 500 K (vacuum)

**Projet
FEDER
IMATOP**

**Linkam Heat Cell
-70 °C to 600 °C
(UV to IR)
+ environment :
N₂, wet air, ...**

Optical Properties

- Sample layout :



- Spectroscopic Ellipsometry :

$$\rho = \frac{r_p}{r_s} = \tan \Psi e^{i\Delta}$$

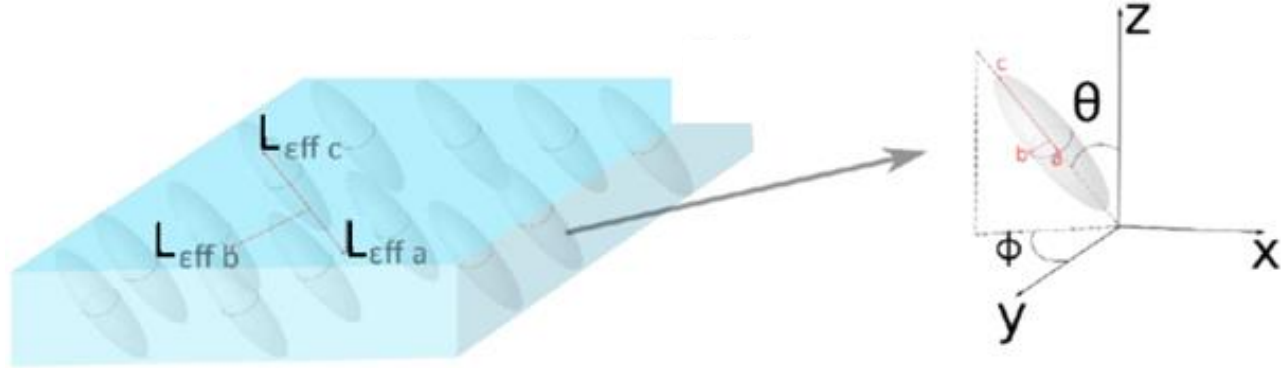
- extract dielectric functions (DFs) $\varepsilon = \varepsilon_1 + i\varepsilon_2$

- Complex heterostructure

- **Identifying the optical indexes of each layer** to unravel the optical properties

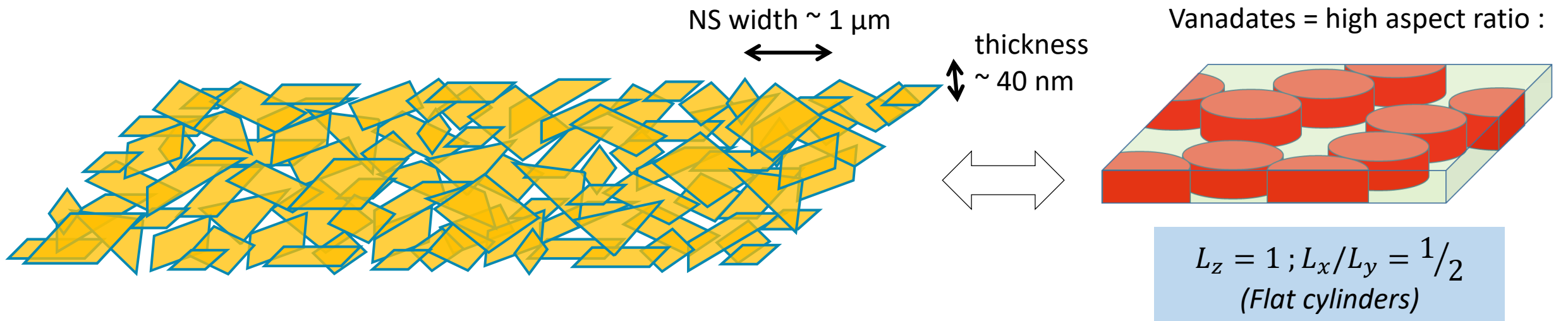
- 70 % crystalline (growth on NS)
- 30 % amorphous (growth on Glass)
- **treat as Effective Medium**

Anisotropic Bruggemann Effective Medium Approximation (ABEMA)



- Analytical model for light scattering on ellipsoidal inclusion (Depolarization factors L_x, L_y, L_z)
- Symetric : volume fraction $f = 0 - 100 \%$

$$f \frac{1 - \epsilon_{eff,j}}{\epsilon_{eff,j} + L_j^D (1 - \epsilon_{eff,j})} + (1 - f) \frac{\epsilon_m - \epsilon_{eff,j}}{\epsilon_{eff,j} + L_j^D (\epsilon_m - \epsilon_{eff,j})} = 0$$



Amorphous CaVO_3 : sample grown @ 400 °C

Layer # 3 = [LAOa Cauchy](#) Thickness # 3 = [5.40 nm](#)

Layer # 2 = [cvo 191213 400degC visir - TL GGG D](#) Thickness # 2 = [40.20 nm](#)

[Show Dialog](#)

- e1 Components
 - Einf = [1.238](#) (fit)
 - UV Pole Amp. = [0.000](#) UV Pole En. = [11.000](#)
 - IR Pole Amp. = [0.000](#)
- e2 Components
 - Oscillator Menu: [Add](#) [Delete](#) [Delete All](#) [Sort](#)
 - Fit Menu: [All](#) [None](#) [Amp.](#) [Br.](#) [En.](#)
 - 1: Type = [Tauc-Lorentz](#) Amp1 = [47.5488](#) (fit)
Br1 = [1.618](#) (fit) Eo1 = [3.902](#) (fit) Eg1 = [2.773](#) (fit)
 - 2: Type = [Drude\(RT\)](#) Resistivity (Ohm·cm)² = [0.002231](#) (fit) Scat. Time (fs)² = [0.381](#) (fit)
 - 3: Type = [Gaussian](#) Amp3 = [4.742767](#) (fit) Br3 = [4.7349](#) (fit) En3 = [8.000](#)
 - 4: Type = [Gaussian](#) Amp4 = [0.644681](#) (fit) Br4 = [8.5239](#) (fit) En4 = [2.173](#) (fit)

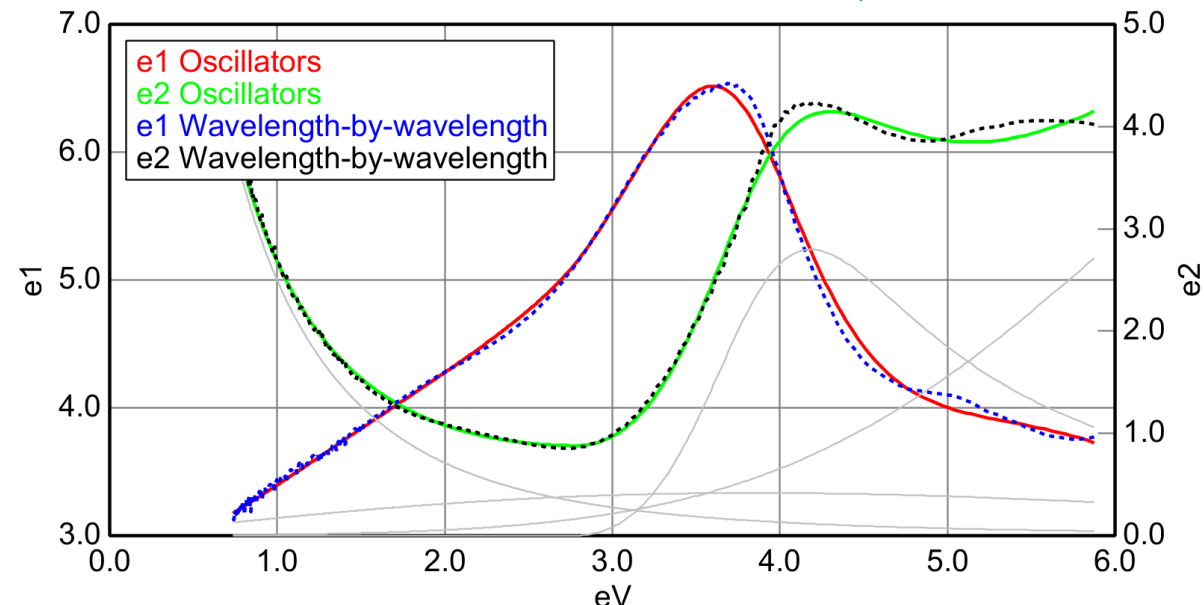
Layer # 1 = [NS EMA TLG - Urbach](#) Thickness # 1 = [3.30 nm](#)

Substrate = [Silice Eagle XG visir genosc fit](#)

Thickness fixed by XRR measurement

direct calculation of ϵ_1 and ϵ_2 + oscillator functions fit

DFs fixed from reference samples



Crystalline CaVO_3 : sample grown @ 500 °C

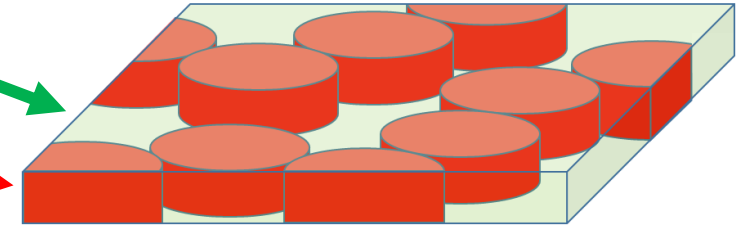
Effective Medium (ABEMA) :

Fitted volume fraction f
of amorphous $\text{CaVO}_3 = 30\%$

→ consistent with AFM / EBSD !

amorphous CaVO_3
(fixed DFs)

crystalline CaVO_3
DFs fitted by
oscillator functions



$$L_z = 1 ; L_x/L_y = 1/2$$

(Flat cylinders)

+ Layer # 3 = [LAOa Cauchy](#) Thickness # 3 = [5.40 nm](#)

- Layer # 2 = [EMA](#) Thickness # 2 = [44.90 nm](#)

of Constituents = 2

- Material 1 = [crystalline CVO](#)

[Show Dialog](#)

- e1 Components

Einf_crystalline CVO = [0.818](#) (fit)

UV Pole Amp_crystalline CVO = [0.0](#)

IR Pole Amp_crystalline CVO = [0.0](#)

- e2 Components

Oscillator Menu: [Add](#) [Delete](#) [Delete](#)

Fit Menu: [All](#) [None](#) [Amp.](#) [Br.](#) [En.](#)

1: Type = [Tauc-Lorentz](#) Amp1_crystalline CVO = [0.795](#) (fit)

2: Type = [Drude\(RT\)](#) Resistivity (CVO) = [0.0](#)

3: Type = [Gaussian](#) Amp3_crystalline CVO = [0.0](#)

4: Type = [Gaussian](#) Amp4_crystalline CVO = [0.0](#)

5: Type = [Gaussian](#) Amp5_crystalline CVO = [5.838524](#) (fit) Br5_crystalline CVO = [2.0](#)

Material 2 = [amorphous CVO](#)

P_amorphous = [30.2](#) (fit)

depolarization (z) = [1.000](#) depolarization (x-y split) = [0.500](#)

Euler Angles: Phi = [0.00](#) Theta = [0.00](#) Psi = [0.00](#)

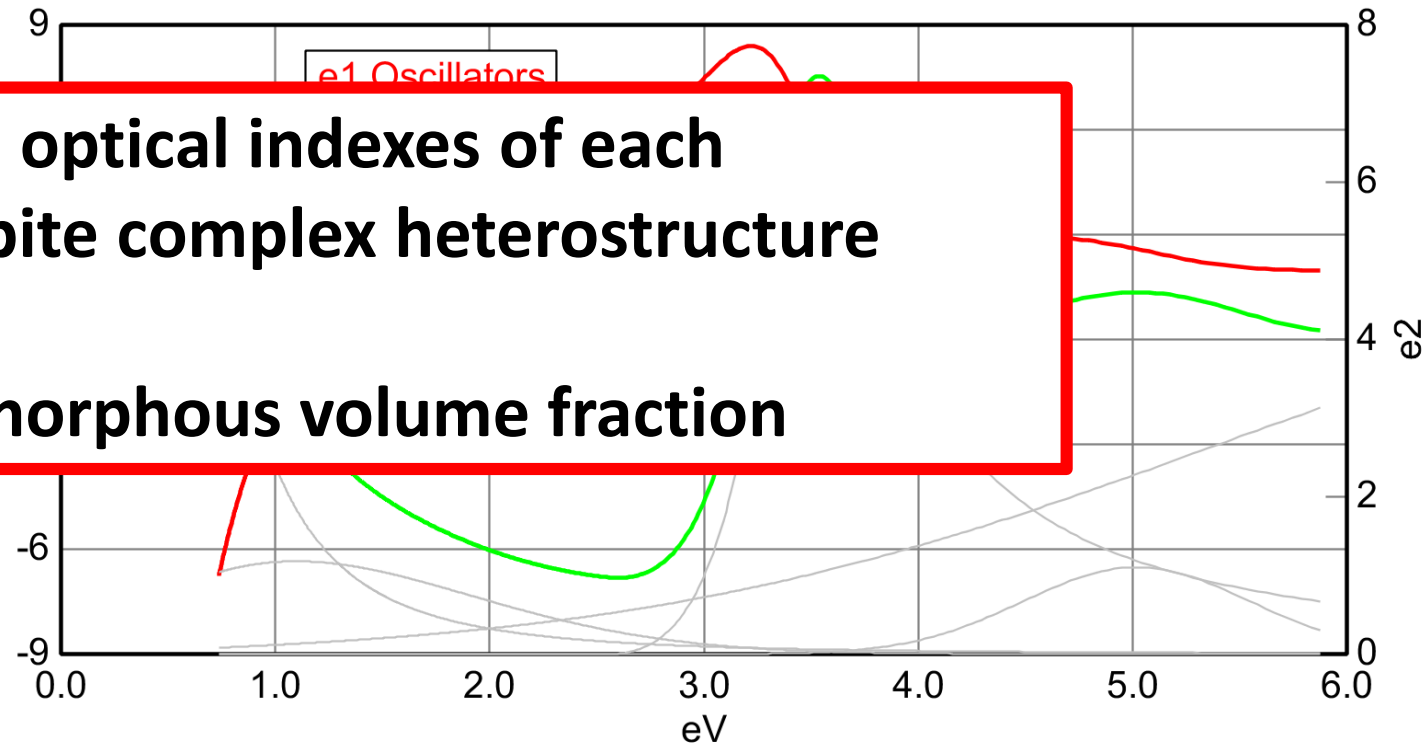
Analysis Mode = [Anisotropic Bruggeman](#)

+ Layer # 1 = [NS EMA TLG - Urbach](#) Thickness # 1 = [3.30 nm](#)

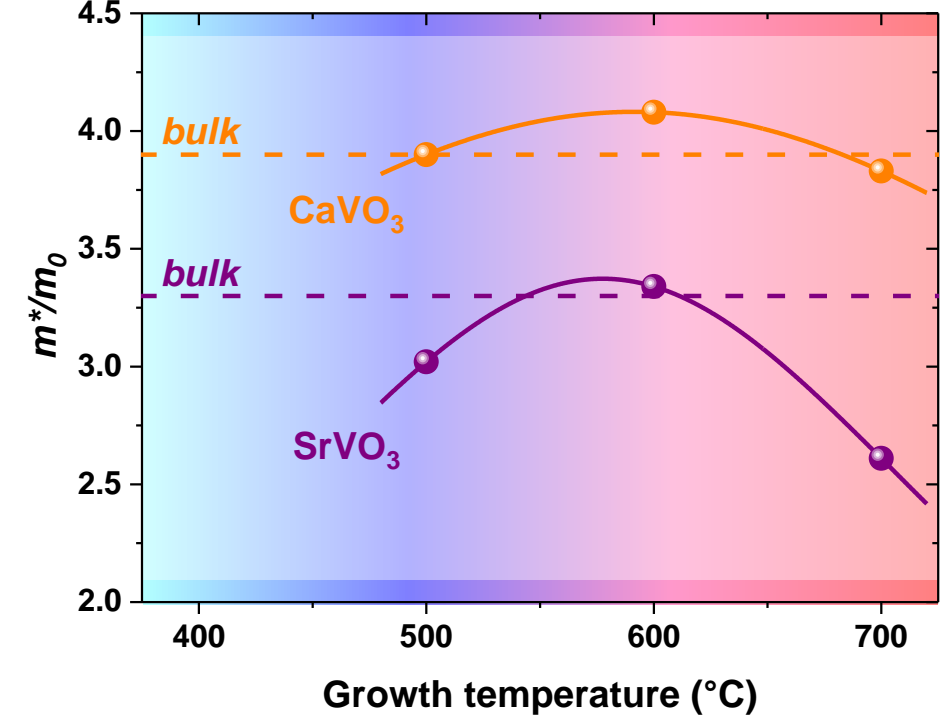
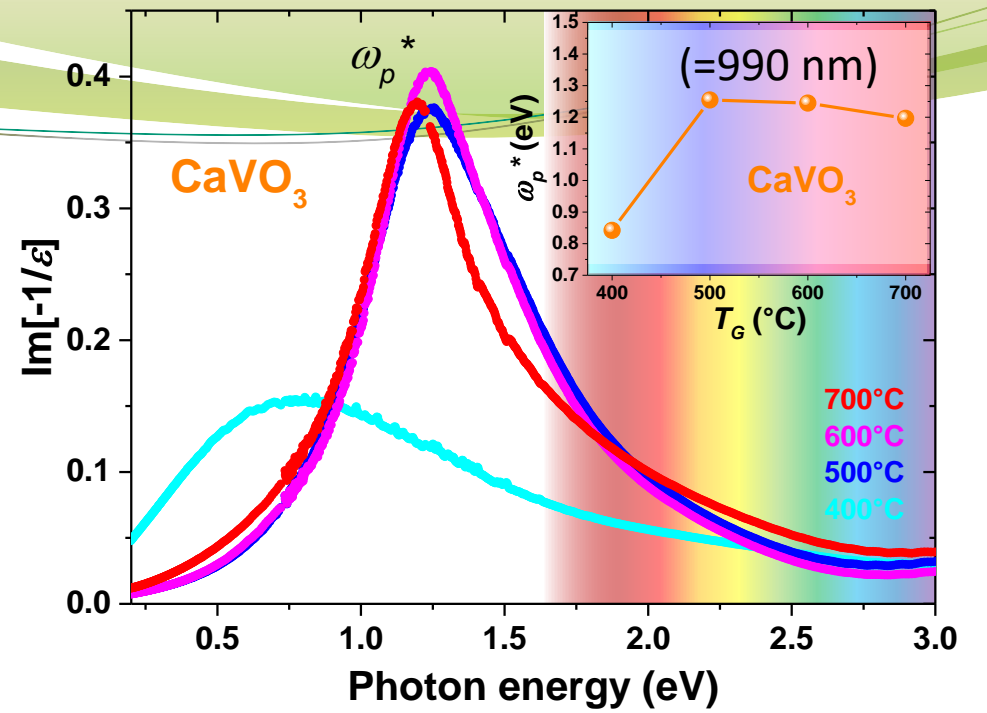
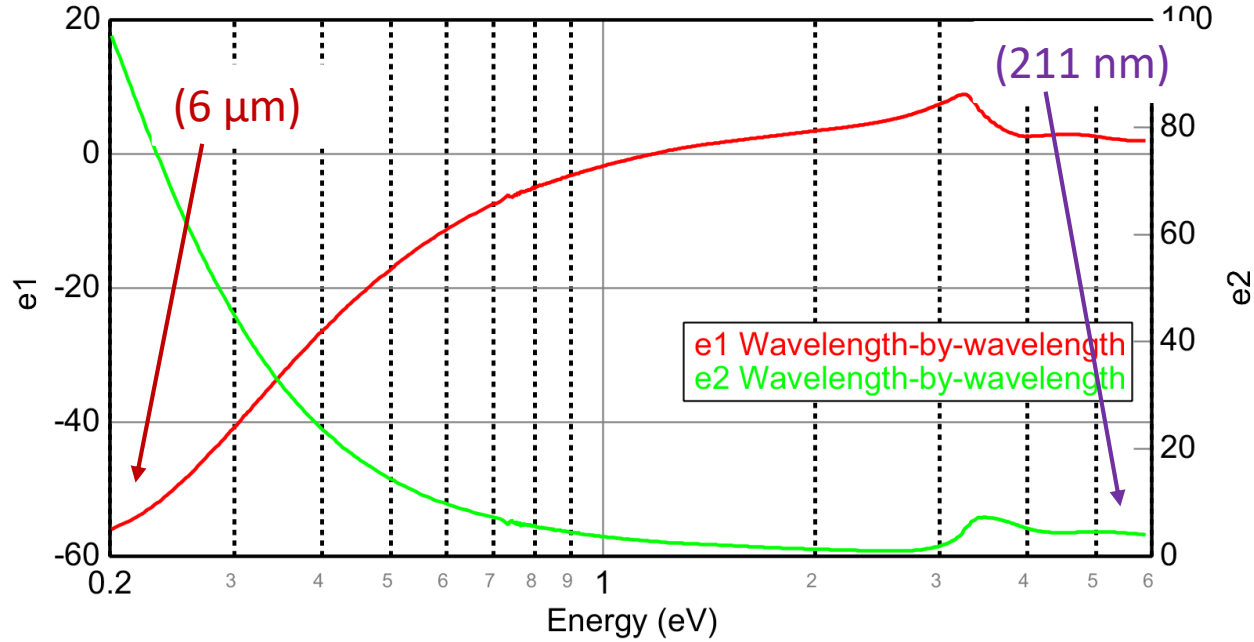
+ Substrate = [Silice Eagle XG visir genosc fit](#)

→ Decorrelate the optical indexes of each component despite complex heterostructure

→ Quantify the amorphous volume fraction



Infrared properties



- Electronic correlation \rightarrow frequency-dependent effective mass m^* and scattering time τ (Extended Drude model) :

$$\epsilon(\omega) = \epsilon_\infty - \frac{\omega_p^2(\omega)}{\omega^2 + i\omega\gamma(\omega)}$$

- Plasma frequency $\omega_p = 1.25$ eV (990 nm) \rightarrow IR range
- m^* close to bulk values \rightarrow relaxation of strain on NS

Comparison : optical vs. electrical properties

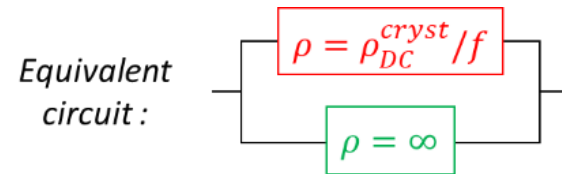
Crystalline phase (ρ_{DC}^{cryst})

$$\text{Total DC resistivity } (\rho_{DC}) = \underbrace{\text{In-grain}}_{\text{Optical resistivity } (\rho_{opt})} + \text{Grain boundary} + \underbrace{\text{Network connectivity}}_{\text{Depolarization factor } L \text{ and Volume fraction } f}$$

Optical resistivity (ρ_{opt})

Depolarization factor L
Volume fraction f

Effective Medium :

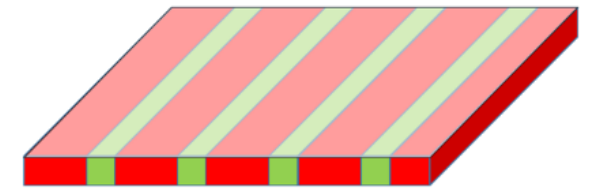
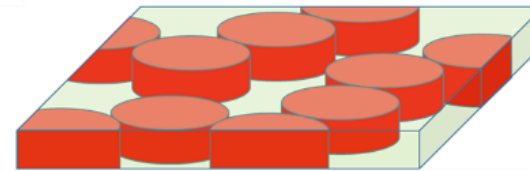
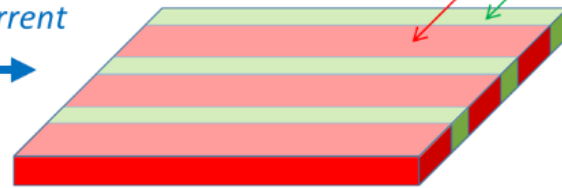


(1) Maximum connectivity :

$$\rho_{DC} = \rho_{DC}^{cryst} / f$$

DC current

crystalline (f)
amorphous ($1 - f$)



(2) In general :

$$\rho_{DC}^{cryst} \geq \rho_{opt}$$

Negligible grain boundary

$$\rightarrow \rho_{DC}^{cryst} = \rho_{opt}$$

Maximum connectivity :

$$\rho_{DC} = \rho_{DC}^{cryst} / f$$

$$L = 0$$

Intermediate connectivity
(Flat cylinders)

$$L = 1/2$$

No percolation :

$$\rho_{DC} = \infty$$

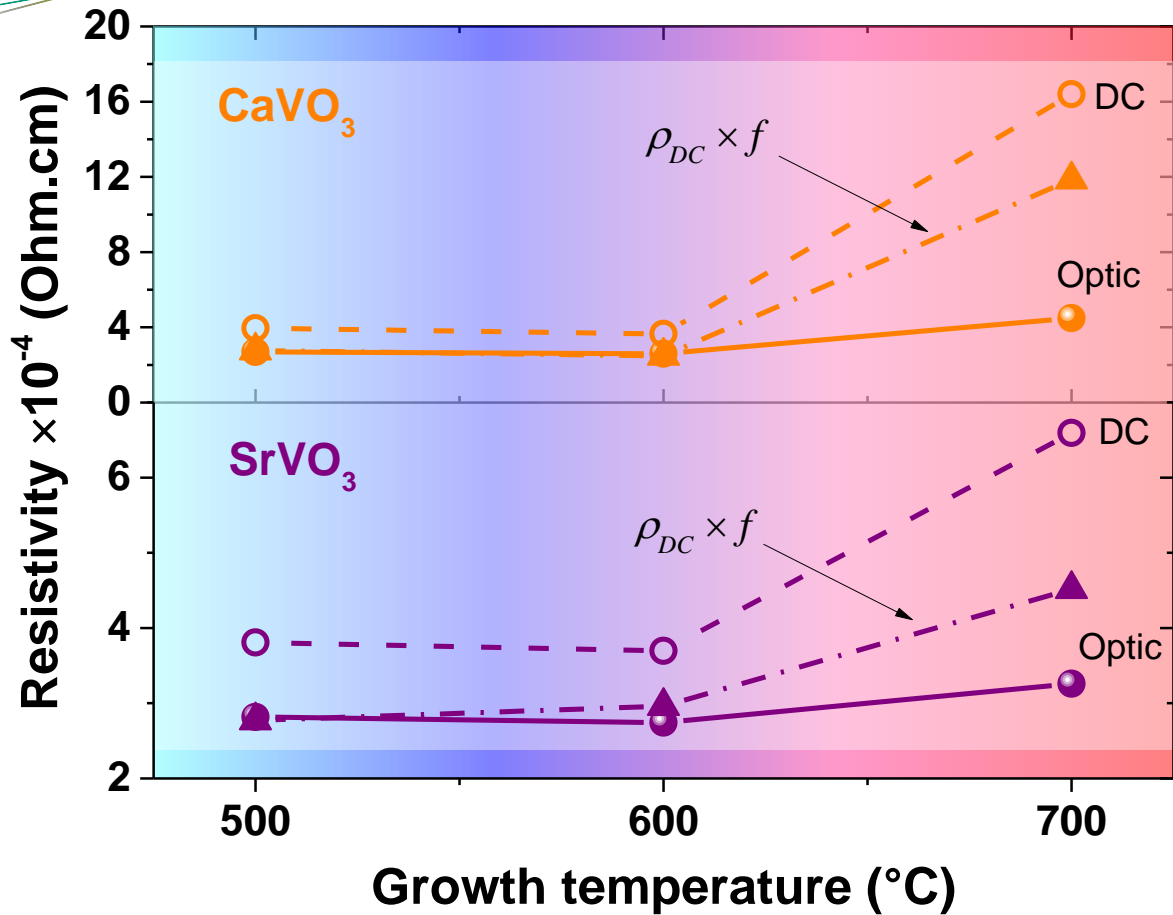
$$L = 1$$



Vanadates on NS :

$$\rho_{DC} = \rho_{opt} / f \rightarrow \text{Maximum connectivity (1) + Negligible grain boundary (2) !}$$

Comparison : optical vs. electrical properties



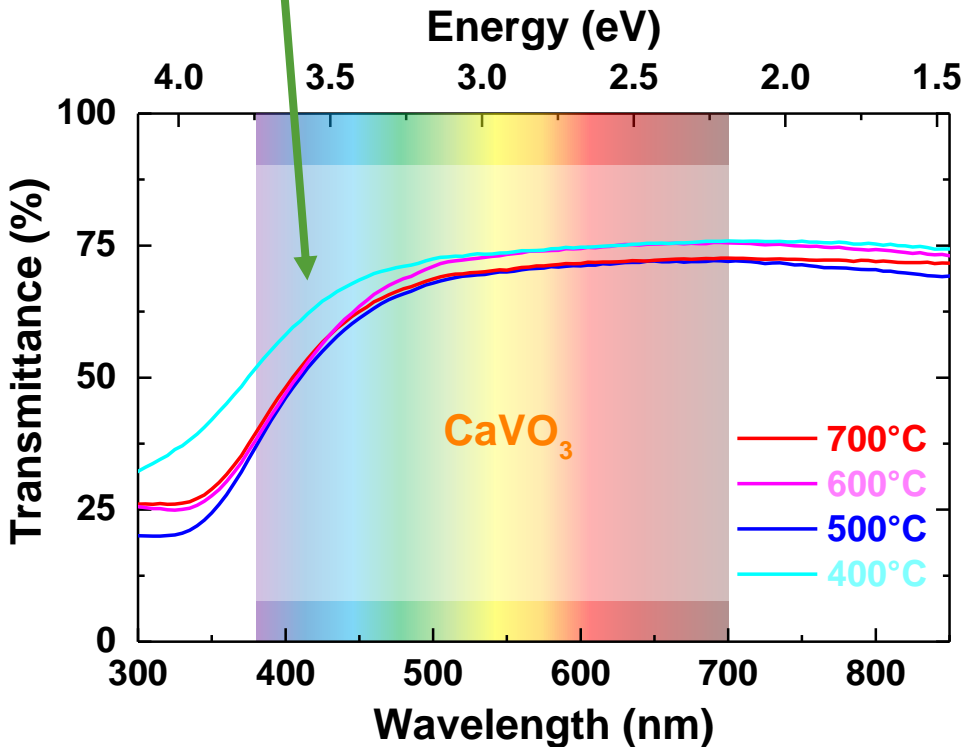
- $\rho_{DC} = \rho_{opt}/f$ @ 500 and 600°C
➔ Maximum connectivity + Negligible grain boundary

- @ 700°C :
 - ρ_{opt} increase ➔ in-grain degradation
 - $\rho_{DC} > \rho_{opt}/f$ ➔ grain boundaries appear

Performance as a transparent conductor

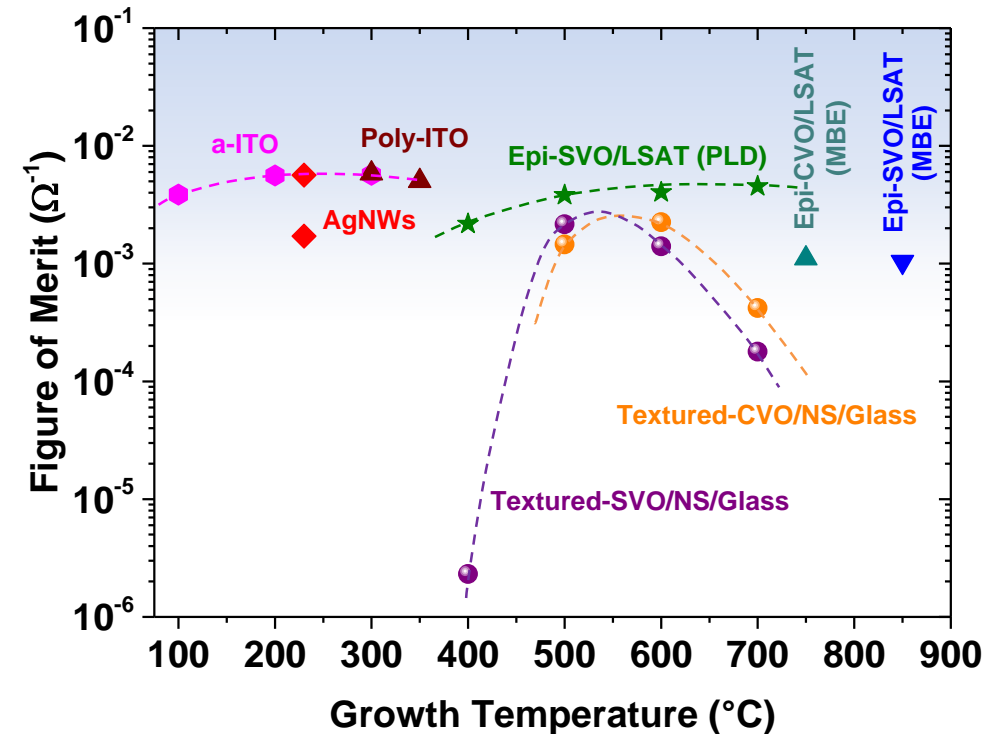
Visible : Transparency = 75 %

Amorphous phase is more transparent
 → increase amorphous proportion ?



Haacke figure of merit = T^{10} / R_{\square}

- as good as epitaxial vanadates or ITO
- reduced growth temperature



Conclusions

- Successful growth of vanadates on Glass substrate thanks to NS
- Performances : as good as ITO or epitaxial vanadates
- Spectroscopic Ellipsometry with EMA :
 - optical indexes of crystalline and amorphous phase
 - proportion of amorphous phase (\leftrightarrow NS coverage)
- Optical-DC comparison with EMA :
 - Good connectivity
 - Negligible grain boundary
- NS coverage = lever to tune properties :
(e.g. : increase amorphous proportion, patterning)

